

RQ5H020SP

Pch -45V -2.0A Power MOSFET

| V_{DSS} | -45V |
|--------------------|----------|
| $R_{DS(on)}(Max.)$ | 190m $Ω$ |
| I _D | -2.0A |
| P_{D} | 1.0W |

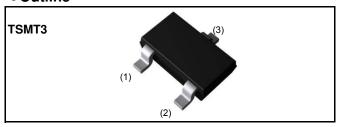
Features

- 1) Low on resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT3).
- 4) Pb-free lead plating; RoHS compliant

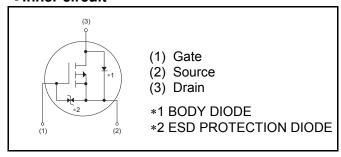
Application

DC/DC converters

Outline



•Inner circuit



Packaging specifications

| | Packaging | Taping |
|------|---------------------------|--------|
| | Reel size (mm) | 180 |
| Typo | Tape width (mm) | 8 |
| Туре | Basic ordering unit (pcs) | 3,000 |
| | Taping code | TL |
| | Marking | FB |

● Absolute maximum ratings(T_a = 25°C)

| Parameter | Symbol | Value | Unit |
|------------------------------|-------------------------|-------------|------|
| Drain - Source voltage | V_{DSS} | –45 | V |
| Continuous drain current | I _D *1 | ±2.0 | А |
| Pulsed drain current | I _{D,pulse} *2 | ±8.0 | А |
| Gate - Source voltage | V_{GSS} | ±20 | V |
| Dowar dissination | P _D *3 | 1.0 | W |
| Power dissipation | P _D *4 | 0.54 | W |
| Junction temperature | T _j | 150 | °C |
| Range of storage temperature | T _{stg} | −55 to +150 | °C |

●Thermal resistance

| Parameter | Symbol | Values | | | Unit |
|--|----------------------|--------|------|------|-------|
| r arameter | | Min. | Тур. | Max. | Offic |
| Thormal registance junction, ambient | R _{thJA} *3 | - | - | 125 | °C/W |
| Thermal resistance, junction - ambient | R _{thJA} *4 | - | - | 232 | °C/W |

●Electrical characteristics(T_a = 25°C)

| Parameter | Symbol | Conditions | Values | | | Unit | |
|--|---|---|-----------------|------|------|-------|--|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | | |
| Drain - Source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V$, $I_D = -1mA$ | -4 5 | 1 | - | V | |
| Breakdown voltage temperature coefficient | $\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$ | I _D = -1mA referenced to 25°C | 1 | -43 | 1 | mV/°C | |
| Zero gate voltage drain current | I _{DSS} | $V_{DS} = -45V, V_{GS} = 0V$ | ı | ı | -1 | μΑ | |
| Gate - Source leakage current | I _{GSS} | $V_{GS} = \pm 20V, V_{DS} = 0V$ | ı | ı | ±10 | μΑ | |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS} = -10V, I_{D} = -1mA$ | -1.0 | ı | -3.0 | V | |
| Gate threshold voltage temperature coefficient | $\frac{\Delta V_{(GS)th}}{\Delta T_{j}}$ | I _D = -1mA referenced to 25°C | - | 3.2 | - | mV/°C | |
| | | V_{GS} = -10V, I_{D} = -2.0A | - | 130 | 190 | | |
| Static drain - source | D *5 | V_{GS} = -4.5V, I_{D} = -2.0A | - | 180 | 260 | mΩ | |
| on - state resistance | $R_{DS(on)}$ | V_{GS} = -4.0V, I_{D} = -2.0A | - | 200 | 280 | 11122 | |
| | | V _{GS} = -10V, I _D = -2.0A, T _j =125°C | ı | 200 | - | | |
| Gate input resistannce | R_G | f = 1MHz, open drain | - | 21 | - | Ω | |
| Transconductance | 9 _{fs} *5 | $V_{DS} = -10V, I_{D} = -2.0A$ | 1.2 | 4.0 | - | S | |

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 $\mu s,~Duty~cycle \leq$ 1%

^{*3} Mounted on a seramic board (30×30×0.8mm)

^{*4} Mounted on a FR4 (12×20×0.8mm)

^{*5} Pulsed

•Electrical characteristics($T_a = 25$ °C)

| Parameter | Symbol | Conditions | Values | | | Unit |
|------------------------------|------------------------|--|--------|------|------|-------|
| - Farameter | Symbol | Conditions | Min. | Тур. | Max. | Offic |
| Input capacitance | C _{iss} | V _{GS} = 0V | - | 500 | - | |
| Output capacitance | C _{oss} | V _{DS} = -10V | - | 80 | - | pF |
| Reverse transfer capacitance | C_{rss} | f = 1MHz | - | 40 | - | |
| Turn - on delay time | t _{d(on)} *5 | $V_{DD} \simeq -25V$, $V_{GS} = -10V$ | - | 8 | - | |
| Rise time | t _r *5 | I _D = -1.0A | - | 10 | - | no |
| Turn - off delay time | t _{d(off)} *5 | $R_L = 25\Omega$ | - | 35 | - | ns |
| Fall time | t _f *5 | $R_G = 10\Omega$ | - | 10 | - | |

•Gate Charge characteristics($T_a = 25$ °C)

| Parameter | Symbol | Conditions | Values | | | Unit |
|----------------------|---------------------|---|--------|------|------|-------|
| - Farameter | Symbol | Conditions | Min. | Тур. | Max. | Offic |
| Total gate charge | ${\sf Q_g}^{^{*5}}$ | $V_{DD}^{2} - 25V$, $I_{D} = -2.0A$ $V_{GS} = -4.5V$ | - | 4.5 | - | |
| Total gate charge | \mathbf{Q}_{g} | $V_{DD}^{\sim} -25V$, $I_{D} = -2.0A$ $V_{GS} = -10V$ | - | 9.5 | - | nC |
| Gate - Source charge | Q _{gs} *5 | $V_{DD}^{\sim} -25V$, $I_{D} = -2.0A$ $V_{GS} = -10V$ | - | 1.6 | - | |
| Gate - Drain charge | Q _{gd} *5 | $V_{GS} = -10V$ | 1 | 1.2 | - | |

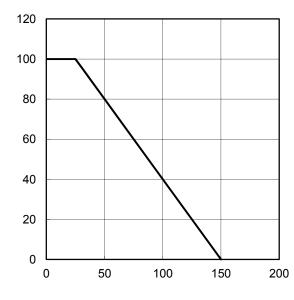
●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

| Parameter | Symbol Conditions - | | Values | | | Unit |
|---|---------------------|----------------------------|--------|------|------|-------|
| r ai ainetei | | | Min. | Тур. | Max. | Offic |
| Inverse diode continuous, forward current | l _S *1 | T _a = 25°C | - | - | -0.8 | А |
| Forward voltage | V _{SD} *5 | $V_{GS} = 0V, I_s = -2.0A$ | - | - | -1.2 | V |

Power Dissipation: P_D/P_D max. [%]

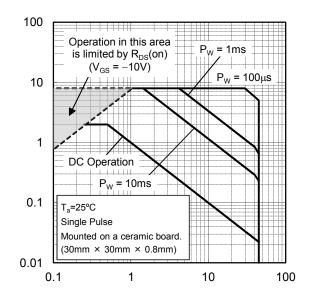
• Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

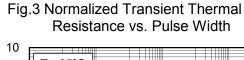


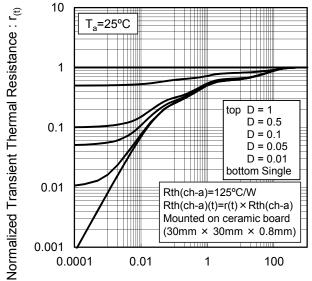
Junction Temperature : Tj [°C]

Fig.2 Maximum Safe Operating Area



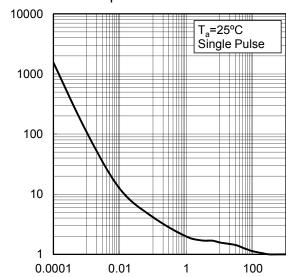
Drain - Source Voltage : -V_{DS} [V]





Pulse Width: Pw [s]

Fig.4 Single Pulse Maxmum Power dissipation



Pulse Width: Pw [s]

Peak Transient Power:P(W)

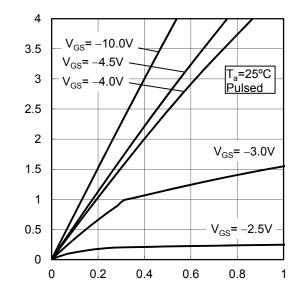
Drain Current: -I_D [A]

Drain Current: -l_D [A]

Drain - Source Breakdown Voltage : - $V_{(BR)DSS}$ [V]

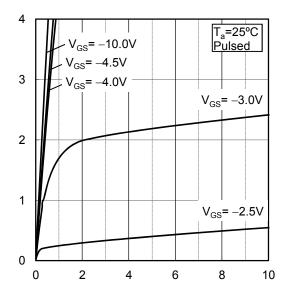
• Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)



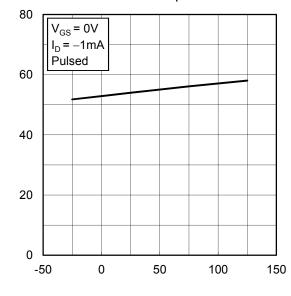
Drain - Source Voltage : -V_{DS} [V]

Fig.6 Typical Output Characteristics(II)



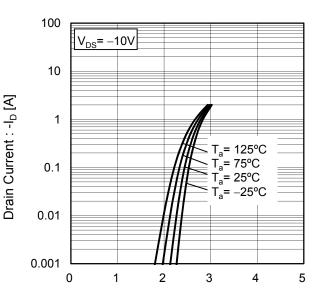
Drain - Source Voltage : -V_{DS} [V]

Fig.7 Breakdown Voltage vs. Junction Temperature



Junction Temperature : T_j [°C]

Fig.8 Typical Transfer Characteristics



Gate - Source Voltage : -V_{GS} [V]

Drain Current: -l_D [A]

Gate Threshold Voltage: -V_{GS(th)} [V]

• Electrical characteristic curves

Fig.9 Gate Threshold Voltage

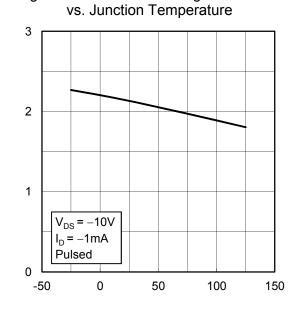
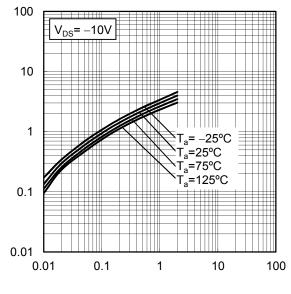


Fig.10 Transconductance vs. Drain Current

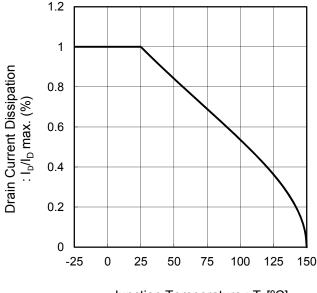


Junction Temperature : T_i [°C]

Drain Current : -I_D [A]

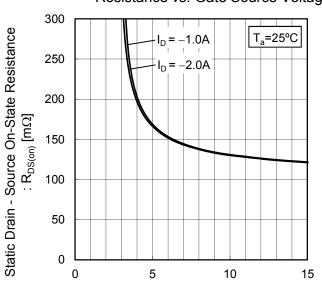
Transconductance: g_{fs} [S]

Fig.11 Drain CurrentDerating Curve



Junction Temperature : T_i [°C]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



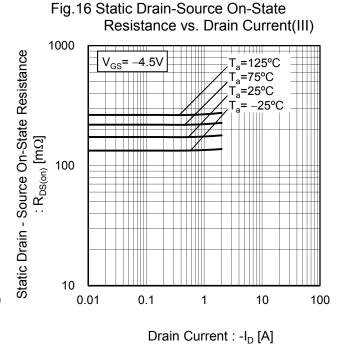
Gate - Source Voltage : -V_{GS} [V]

• Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I) 1000 T₂=25°C Static Drain - Source On-State Resistance V_{GS}= -4.0V V_{GS}= -4.5V -10V $:R_{\text{DS(on)}}\left[m\Omega \right]$ 100 10 0.01 0.1 1 10 100 Drain Current : -I_D [A]

Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature 250 Static Drain - Source On-State Resistance 200 150 $:R_{\text{DS(on)}}\left[\text{m}\Omega\right]$ 100 50 $V_{GS} = -10V$ $I_{D} = -2.0A$ Pulsed 0 -50 -25 0 25 50 75 100 125 150 Junction Temperature : T_i [°C]

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II) 1000 Static Drain - Source On-State Resistance =125°C T_a=75°C Ta=25°C -25°C $: R_{DS(on)} \left[m\Omega \right]$ 100 10 0.01 0.1 1 10 100 Drain Current : -I_D [A]

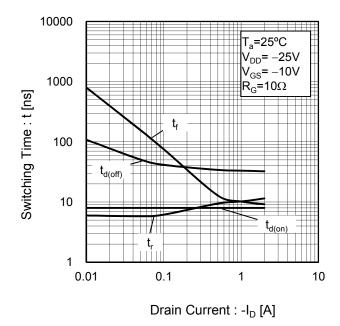


•Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV) 1000 Static Drain - Source On-State Resistance =75°C 25°C -25°C $:R_{\text{DS(on)}}\left[\text{m}\Omega \right]$ 100 10 0.01 0.1 1 10 100 Drain Current : -I_D [A]

Fig.18 Typical Capacitance vs. Drain - Source Voltage $\begin{array}{c} 10000 \\ \hline 10000 \\ \hline 1000 \\ \hline \\ 1000 \\$

Fig.19 Switching Characteristics



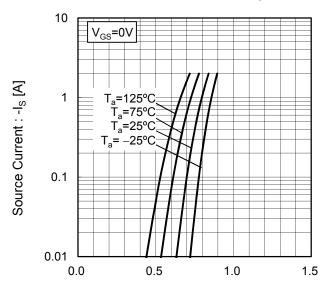
Gate - Source Voltage : - V_{GS} [V]

10 $T_a=25^{\circ}C$ $V_{DD}=-25V$ $I_D=2A$ $R_G=10\Omega$

Fig.20 Dynamic Input Characteristics

•Electrical characteristic curves

Fig.21 Source Current vs. Source Drain Voltage



Source-Drain Voltage : $-V_{SD}$ [V]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

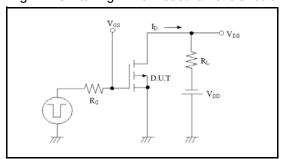


Fig.2-1 Gate Charge Measurement Circuit

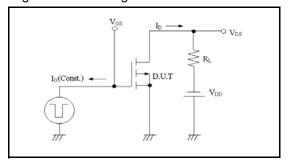


Fig.1-2 Switching Waveforms

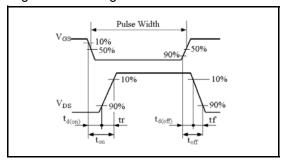
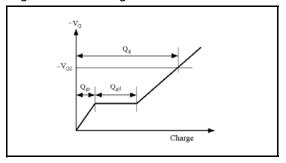
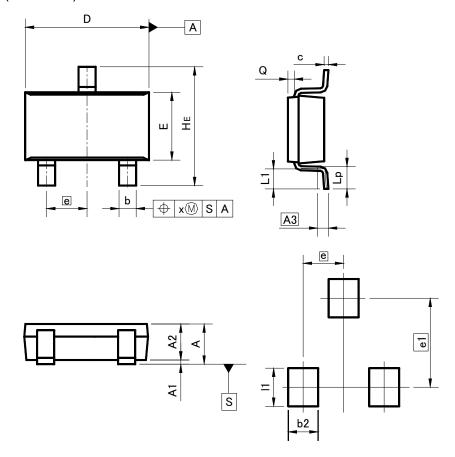


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)





Patterm of terminal position areas

| DIM | MILIM | ETERS | INC | HES |
|-----|-------|-------|-------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | _ | 1.00 | ı | 0.039 |
| A1 | 0.00 | 0.10 | 0 | 0.004 |
| A2 | 0.75 | 0.95 | 0.03 | 0.037 |
| A3 | 0.3 | 25 | 0.0 | 01 |
| b | 0.35 | 0.50 | 0.014 | 0.02 |
| С | 0.10 | 0.26 | 0.004 | 0.01 |
| D | 2.80 | 3.00 | 0.11 | 0.118 |
| Е | 1.50 | 1.80 | 0.059 | 0.071 |
| е | 0.9 | 95 | 0.0 | 04 |
| HE | 2.60 | 3.00 | 0.102 | 0.118 |
| L1 | 0.30 | 0.60 | 0.012 | 0.024 |
| Lp | 0.40 | 0.70 | 0.016 | 0.028 |
| Q | 0.05 | 0.25 | 0.002 | 0.01 |
| х | _ | 0.20 | | 0.008 |

| DIM | MILIMI | ETERS | INCHES | | |
|---------|--------|-------|--------|-------|--|
| I DIIVI | MIN | MAX | MIN | MAX | |
| e1 | 2. | 2.10 | | 08 | |
| b2 | | 0.70 | - | 0.028 | |
| 11 | _ | 0.90 | _ | 0.035 | |

Dimension in mm/inches

Rev.003

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|---------|-----------|------------|----------|
| CLASSⅢ | CL ACCIII | CLASS II b | CL ACCTI |
| CLASSIV | CLASSⅢ | CLASSⅢ | CLASSIII |

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 - [f] Sealing or coating our Products with resin or other coating materials
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- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

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 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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